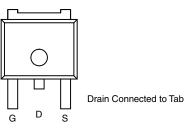


# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0063			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.0069			
I <sub>D</sub> (A)	97			
Configuration	Single			



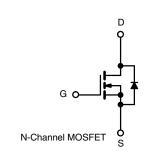


Top View

### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- 100 % Rg and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD97N06-6m3L-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> =	25 °C, unles	s otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	v
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	97	
Continuous Drain Current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	56	
Continuous Source Current (Diode Conduction) <sup>a</sup>		IS	100	A
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	290	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	45	
Single Pulse Avalanche Energy		E <sub>AS</sub>	101	mJ
Marine Davies Diasia attant	T <sub>C</sub> = 25 °C	Р	136	W
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	45	vv
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	C/W

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

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# SQD97N06-6m3L



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	60	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$		2.0	2.5	v
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 25 A	-	0.0050	0.0063	
Drain-Source On-State Resistance <sup>a</sup>	Б	$V_{GS} = 10 V$	$I_D = 25 \text{ A},  \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	-	0.0117	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 25 A, T <sub>J</sub> = 175 °C	-	-	0.0149	Ω
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 20 A	-	0.0055	0.0069	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 25 A	-	177	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	4844	6060	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	441	555	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	200	250	
Total Gate Charge <sup>c</sup>	Qg			-	82	125	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 50 \text{ A}$	-	14.5	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	13.5	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	1	2	3	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	14	21	
Rise Time <sup>c</sup>	t <sub>r</sub>	- V <sub>DD</sub> =	= 30 V, R <sub>I</sub> = 0.6 Ω	-	5	8	1
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		$V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$	-	41	62	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	7	11	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	290	Α
	OW						

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

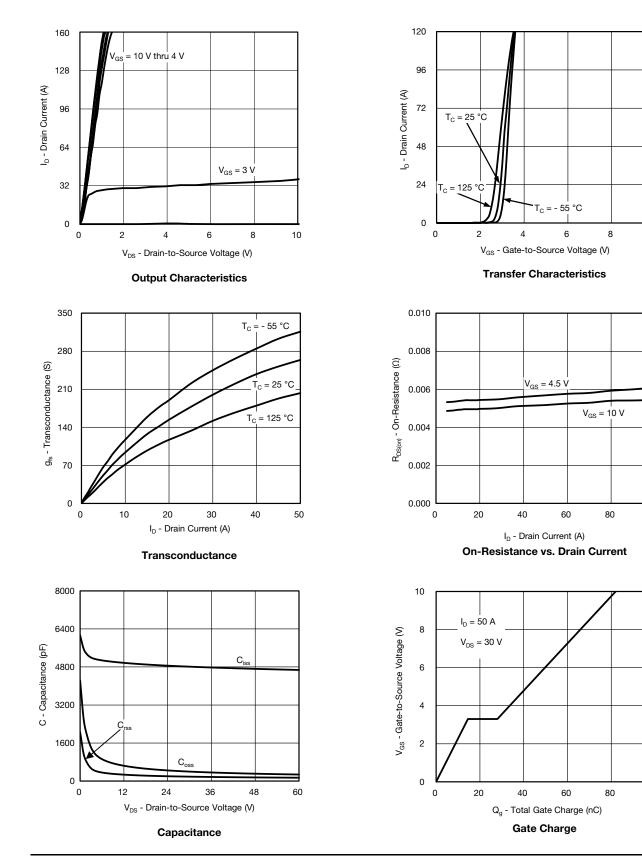
2



10

100

## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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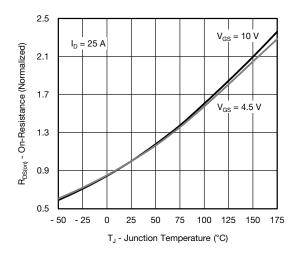
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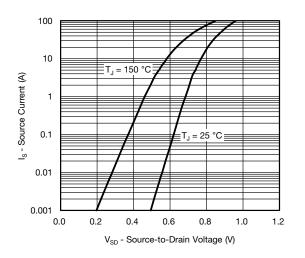




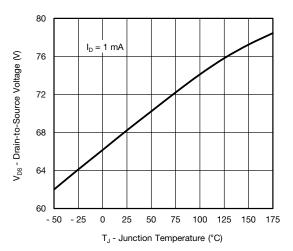
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



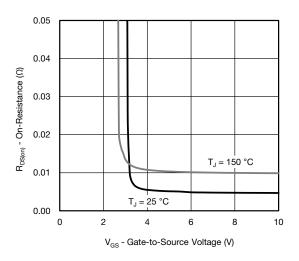
**On-Resistance vs. Junction Temperature** 



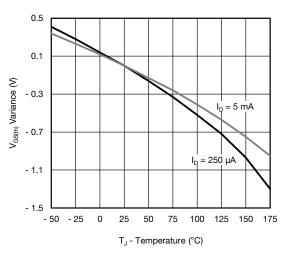
Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature



**On-Resistance vs. Gate-to-Source Voltage** 



**Threshold Voltage** 

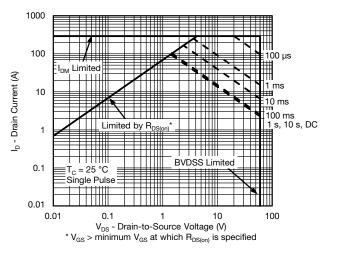
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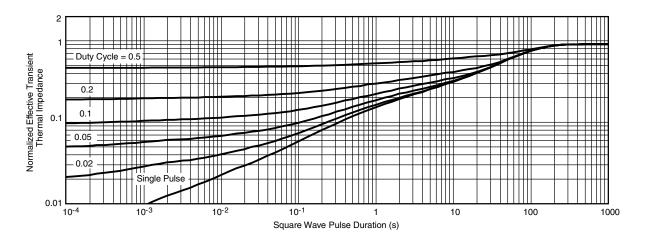


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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



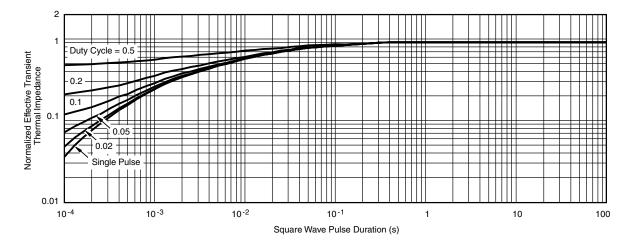
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

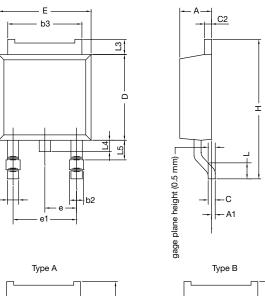
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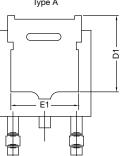
Document Number: 62897



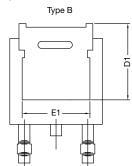


TO-252AA Case Outline





b



MIN.       2.18       -       0.64       0.76       4.95       0.46       0.46       5.97       4.10	MAX. 2.38 0.127 0.88 1.14 5.46 0.61 0.89 6.22	MIN. 0.086 - 0.025 0.030 0.195 0.018 0.018 0.235	MAX. 0.094 0.005 0.035 0.045 0.215 0.024 0.035 0.245
- 0.64 0.76 4.95 0.46 0.46 5.97 0.64 0.65 0.65 0.65 0.65 0.65 0.65 0.65 0.65	0.127 0.88 1.14 5.46 0.61 0.89 6.22	- 0.025 0.030 0.195 0.018 0.018	0.005 0.035 0.045 0.215 0.024 0.035
0.64   0.76   4.95   0.46   0.46   5.97	0.88 1.14 5.46 0.61 0.89 6.22	0.025 0.030 0.195 0.018 0.018	0.035 0.045 0.215 0.024 0.035
0.76 4.95 0.46 0.46 5.97	1.14 5.46 0.61 0.89 6.22	0.030 0.195 0.018 0.018	0.045 0.215 0.024 0.035
4.95 0.46 0.46 5.97	5.46 0.61 0.89 6.22	0.195 0.018 0.018	0.215 0.024 0.035
0.46 0.46 5.97	0.61 0.89 6.22	0.018 0.018	0.024 0.035
0.46 5.97	0.89 6.22	0.018	0.035
5.97	6.22		
		0.235	0.245
4.10			0.240
	-	0.161	-
6.35	6.73	0.250	0.265
4.32	-	0.170	-
9.40	10.41	0.370	0.410
2.28 BSC		0.090	BSC
4.56 BSC		0.180	BSC
1.40	1.78	0.055	0.070
0.89	1.27	0.035	0.050
-	1.02	-	0.040
1.01	1.52	0.040	0.060
	4.32 9.40 2.28 B 4.56 B 1.40 0.89 -	4.32     -       9.40     10.41       2.28 BSC     4.56 BSC       1.40     1.78       0.89     1.27       -     1.02	4.32     -     0.170       9.40     10.41     0.370       2.28 BSC     0.090       4.56 BSC     0.180       1.40     1.78     0.055       0.89     1.27     0.035       -     1.02     -

### Notes

• Dimension L3 is for reference only

• Dimension D1 and E1 on type A and B is the same

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## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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